

**BTCSVI / BTECVI / BTELVI**

**Term-End Examination**

**December, 2011**

**BIEL-001 : BASICS OF ELECTRONICS  
ENGINEERING**

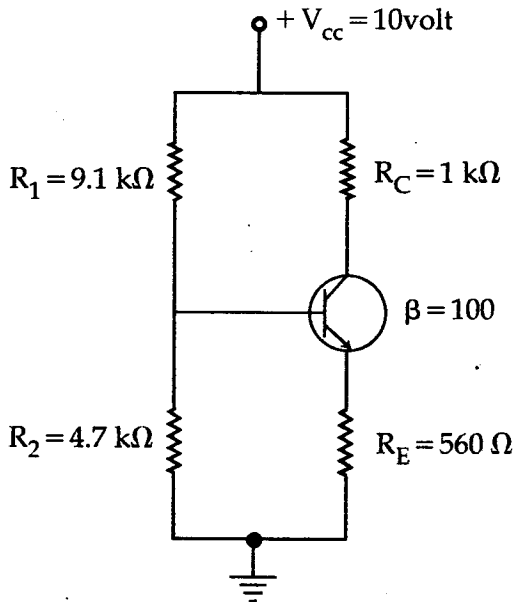
*Time : 3 hours*

*Maximum Marks : 70*

- Note :** 1. Attempt *any five* questions.  
2. All questions carry *equal* marks.

1. (a) What do you understand by semiconductors ? Explain the properties of semiconductor materials. 7
- (b) Draw and explain the energy band model of semiconductors. 7
2. (a) What do you understand by excess carriers in semiconductors ? Also explain continuity equation. 7
- (b) Explain the construction and working of PIN diode with neat diagram. 7

3. (a) Derive the relation between  $\alpha$  and  $\beta$  of BJT. 7  
(b) Calculate the Q point for the voltage divider bias circuit shown in figure (1). 7  
Assume that the Transistor is a silicon transistor with  $\beta = 100$



4. (a) Explain with neat diagram the Ebers Moll model for BJT. 7  
(b) Explain the construction and principle of operation for N channel JFET. 7
5. (a) Explain the construction and working of Depletion type MOSFET. 7

- (b) What do you understand by CMOS ? Also explain the frequency limitation of transistor. 7
6. (a) What are rectifiers ? Explain the working of Bridge rectifier with output waveforms. 7
- (b) Explain with neat diagrams the BJT configurations. 7
7. Attempt *any two* parts of the following.  
(Short Notes) 2x7=14
- (a) Tunnel diode
- (b) Voltage Multipliers
- (c) Phototransistors
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